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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: YANG, TSUN-NEG

SERIAL NO.: 10/715,982

ART UNIT: 2881

FILED: NOVEMBER 18, 2003

EXAMINER: Quash, A.G.

TITLE: ION IMPLANTING APPARATUS

AMENDMENT "A"

Director of the U.S. Patent  
and Trademark Office  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Office Action of October 5, 2004, a response being due on January 5, 2005,  
please amend the above-identified application as follows:

Amendment A: SPECIFICATION

On page 5, paragraph [0014], revise as follows:

The wafer cassette 20 comprises a plurality of irradiation trays 22, and each irradiation tray 22 can load a piece of wafer 12. The implanting base 60 comprises a guiding slot 62 for guiding the irradiation tray 22. The ion implanting apparatus 10 can further comprises an ~~isolative~~ insulative sleeve 64 with a guiding slot 65 allowing the irradiation trays 22 to pass through and a current integrator 66 electrically connected to the implanting base 60. The implanting base 60 comprises two guiding pillars 61 with a guiding trench 62 for guiding the irradiation tray 22 and a top beam 63 connected to the two pillars 61, wherein the guiding pillars 61 are positioned at two sides of the guiding slot 65, respectively. The implanting base 60 is positioned on the isolative sleeve 64 to be insulated from other components in the implanting chamber 30. Consequently, the electric current generated by all ions irradiated onto the wafer 12 can be conducted to the current integrator 66, and the ion implanting dosage of the wafer 12 can be calculated by the integration of the electric current with the implanting time.